General Description

UNIVERSAL PARTS UPD4N60 and UPI4N60 have been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications.By providing low $R_{DS(on)}$, C_{iss} and C_{rss} along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

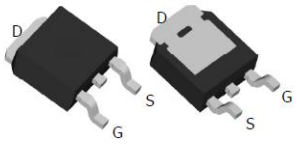
Product Summary

V_{DS}	600V@150℃
I_D (at V_{GS}=10V)	4A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 2.8&

100% UIS Tested!

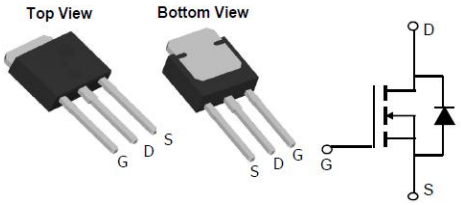
100% R_g Tested!

TO252
DPAK



UPD4N60

TO251



UPI4N60

Absolupe Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	600	V
Gate-Source Voltage		V_{GS}	±30	V
Continuous Drain Current [B]	T_C=25°C	I_D	4	A
	T_C=100°C		2.6	
Pulsed Drain Current [C]		I_{DM}	14	
Avalanche Current [C]		I_{AR}	2.8	A
Repetitive avalanche energy [C]		E_{AR}	118	mJ
Single plused avalanche energy [H]		E_{AS}	235	mJ
MOSFET dv/dt ruggedness		dv/dt	50	V/ns
Peak diode recovery dv/dt			5	
Power Dissipation [B]	T_C=25°C	P_D	104	W
	Derate above 25 C°		0.83	W/ C°
Junction and Storage Temperature Range		T_J, T_{STG}	-50 to 150	°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300	°C

Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Units
Maximum Junction-to-Ambient [A,G]	R\JA	43	55	°C/W
Maximum Case-to-sink [A]	R\CS	-	0.5	°C/W
Maximum Junction-to-Case [D,F]	R\JC	1	1.2	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250μA, V_{GS}=0V, T_J=25°C	600			V
		I_D=250μA, V_{GS}=0V, T_J=150°C		700		
BV_{DSS} /ΔTJ	Zero Gate Voltage Drain Current	ID=250μA, VGS=0V		0.67		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=600V, V_{GS}=0V			1	∝A
		V_{DS}=480V, T_J=125°C			10	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±30V			±100	nℑ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=5V, I_D=250∝A	3.4	4.1	4.5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=2A		2.2	2.8	&
g_{FS}	Forward Transconductance	V_{DS}=40V, I_D=2A		6		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.76	1	V
I_S	Maximum Body-Diode Continuous Current			4		A
I_{SM}	Maximum Body-Diode Pulsed Current			14		A
DYNAMIC PARAMETERS						
C_{iss}	Inpup Capacitance	V_{GS}=0V, V_{DS}=25V, f=1MHz	420	528	640	pF
C_{oss}	Ouppup Capacitance		35	53	70	pF
C_{rss}	Reverse Transfer Capacitance		2.5	4.8	7	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	1.2	2.5	3.8	&
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=480V, I_D=4A	9.5	12	14.5	nC
Q_{gs}	Gate Source Charge		2.8	3.6	4.5	nC
Q_{gd}	Gate Drain Charge		2.2	4.4	6.6	nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=300V, I_D=4A, R_G=25&		17		ns
t_r	Turn-On Rise Time			26		ns
$t_{D(off)}$	Turn-Off DelayTime			34		ns
t_f	Turn-Off Fall Time			21		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=4A,dI/dt=100A/∝s,V_{DS}=100V	150	190	230	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=4A,dI/dt=100A/∝s,V_{DS}=100V	1.9	2.4	3	∝C

A. The value of $R_{\theta JA}$ is measured with the device in a still air environment with T_A =25℃.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150℃ in a TO252 package, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150℃.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 ∝s pulses, dupy cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150℃.

G.These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25℃.

H. L=60mH, I_{AS}=2.8A, V_{DD}=150V, R_G=10Ω, Starting T_J=25℃

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

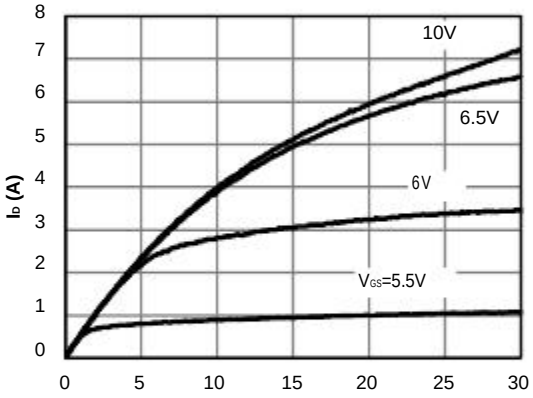


Fig 1: On-Region Characteristics

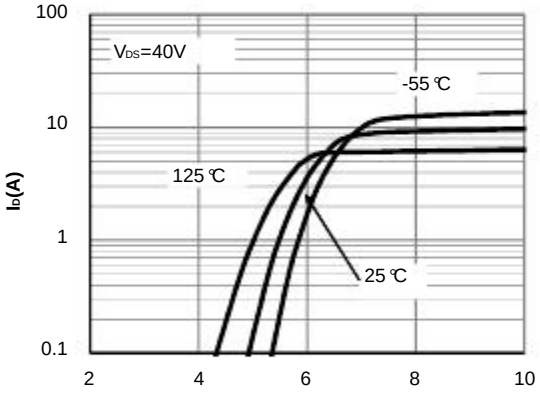


Figure 2: Transfer Characteristics

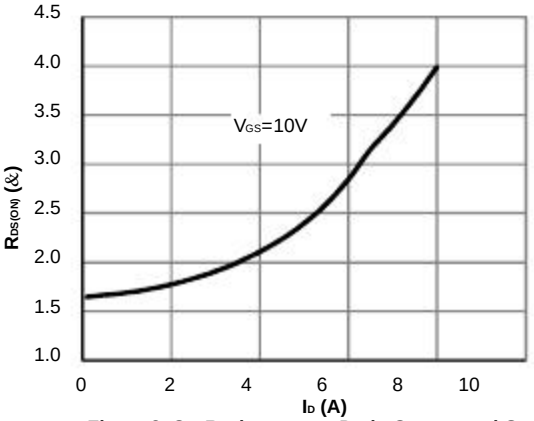


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

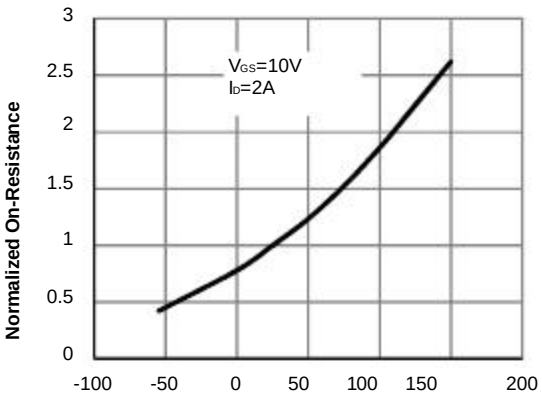


Figure 4: On-Resistance vs. Junction Temperature

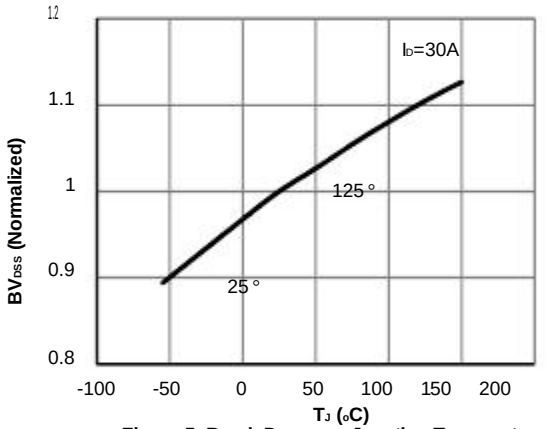


Figure 5: Break Down vs. Junction Temperature

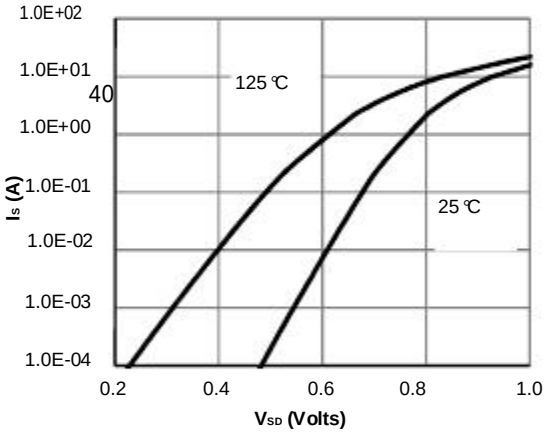


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

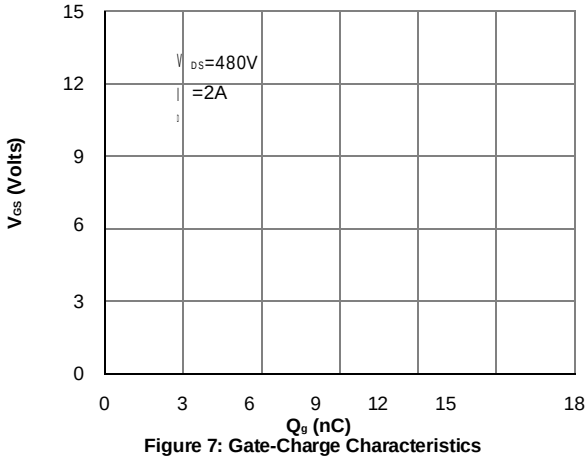


Figure 7: Gate-Charge Characteristics

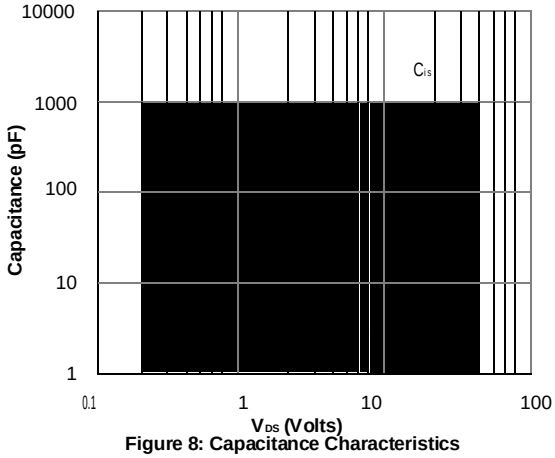


Figure 8: Capacitance Characteristics

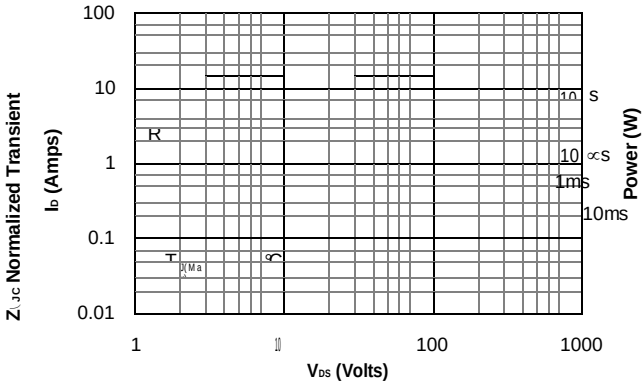


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

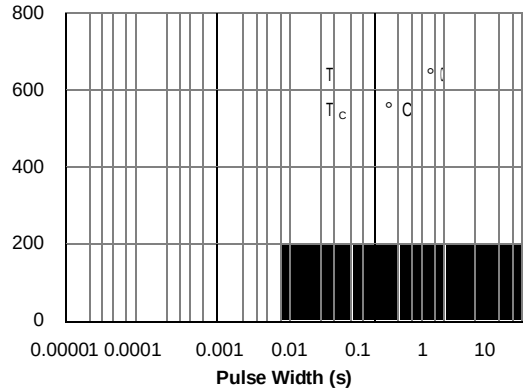


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

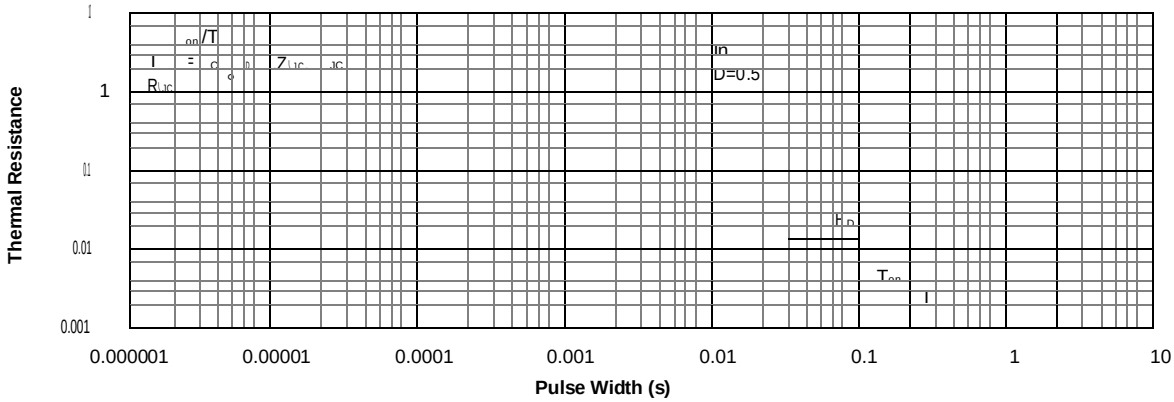


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

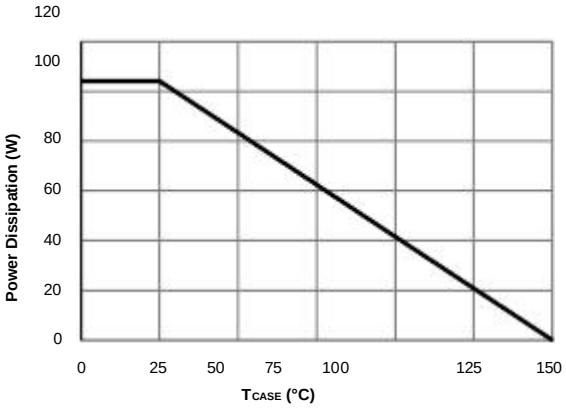


Figure 12: Power De-rating (Note B)

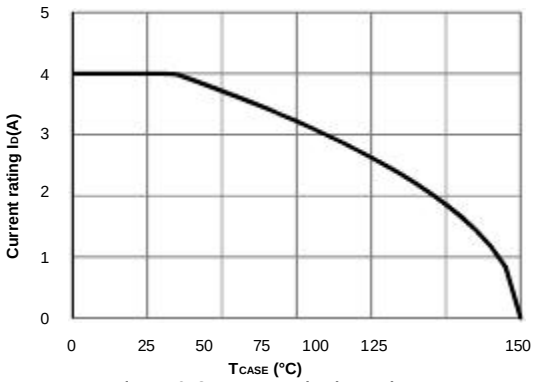


Figure 13: Current De-rating (Note B)

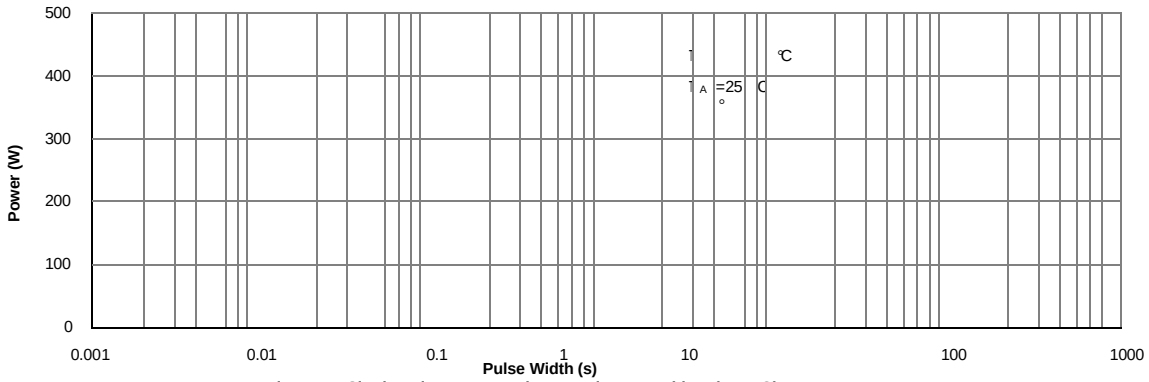


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note G)

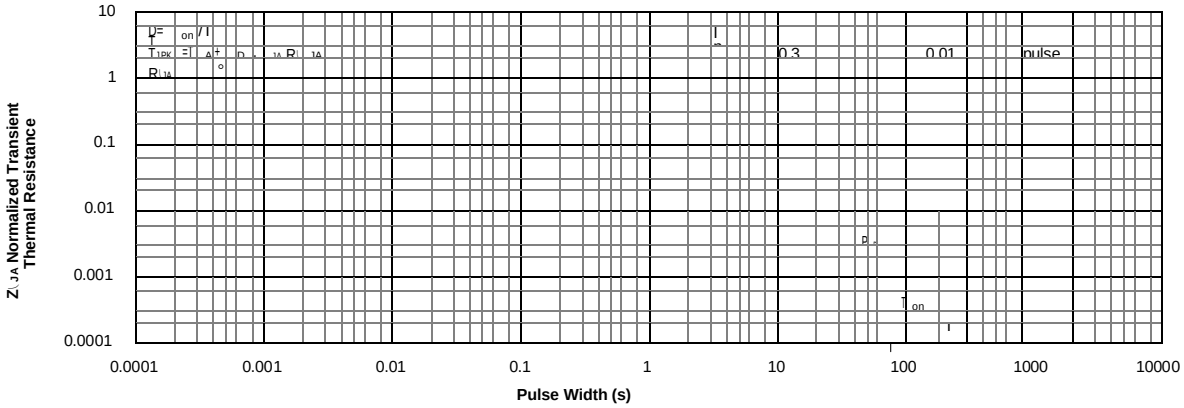
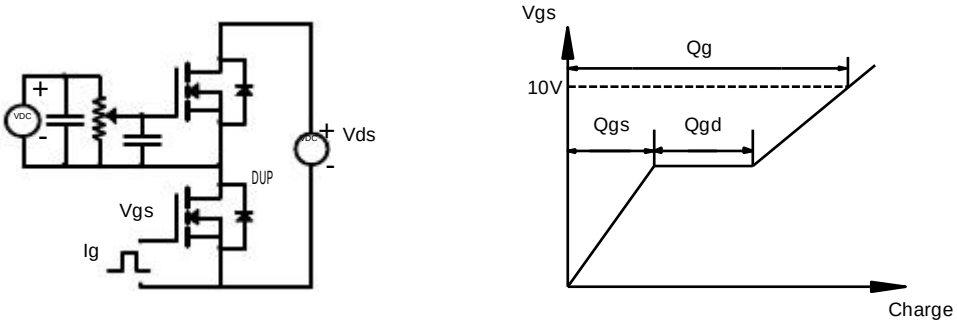
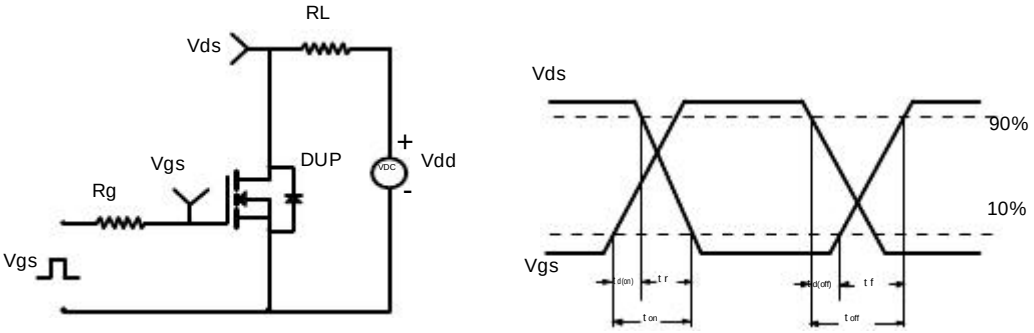


Figure 15: Normalized Maximum Transient Thermal Impedance (Note G)

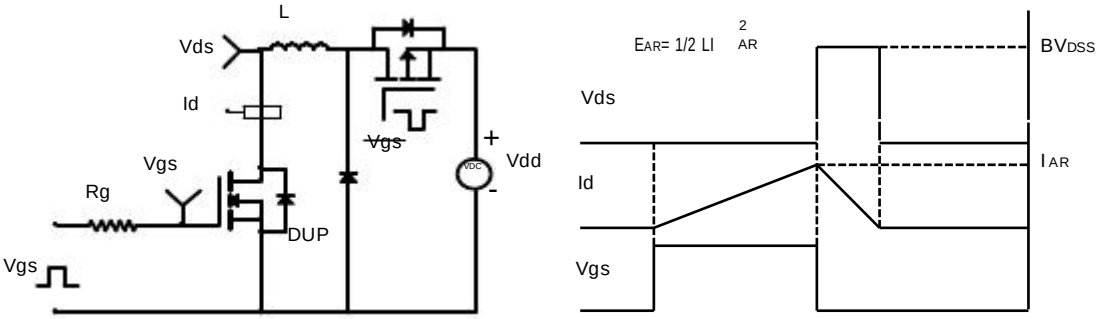
Gate Charge Test Circuit & Waveform



Res istive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Tes t Circuit & Waveforms